

L Number	Hits	Search Text	DB	Time stamp
1	323	semiconductor and (complementary adj bipolar adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/25 14:24
2	143	(semiconductor and (complementary adj bipolar adj transistor) ) and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/25 14:25
3	131	((semiconductor and (complementary adj bipolar adj transistor) ) and electrode) and emitter and base and collector	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/25 14:25
4	83	((semiconductor and (complementary adj bipolar adj transistor) ) and electrode) and emitter and base and collector) and ((polycrystal\$4 adj (silicon or si)) or polysilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/25 14:26

L Number	Hits	Search Text	DB	Time stamp
1	35603	semiconductor and -(bipolar adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/25 14:49
2	9672	(semiconductor and (bipolar adj transistor)) and ((polycrystal\$4 adj (silicon or si)) or polysilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/25 14:50
3	534	((semiconductor and (bipolar adj transistor)) and ((polycrystal\$4 adj (silicon or si)) or polysilicon)) and (rapid adj thermal adj anneal\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/25 14:51
4	6	((semiconductor and (bipolar adj transistor)) and ((polycrystal\$4 adj (silicon or si)) or polysilicon)) and (rapid adj thermal adj anneal\$3)) and (residual adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/25 14:51